2.5V Drive Nch + Nch MOSFET

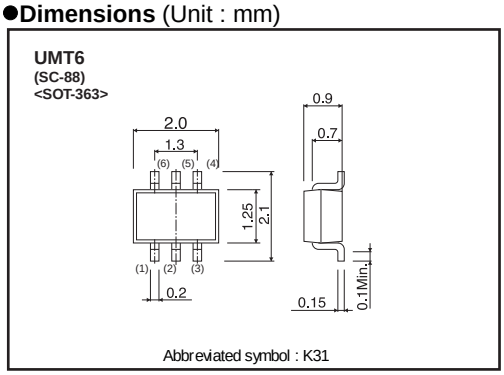
UM6K31N

●Structure
Silicon N-channel MOSFET

●Features
1) High speed switing.
2) Small package(UMT6).
3) Low voltage drive(2.5V drive).

●Application
Switching

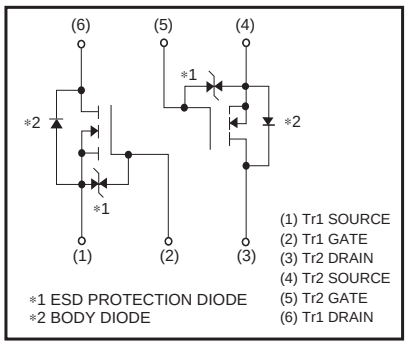
●Dimensions (Unit : mm)



●Packaging specifications

Type	Package	Taping
	Code	TN
	Basic ordering unit (pieces)	3000
UM6K31N		O

●Inner circuit



●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	60	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±250	mA
	Pulsed	I_{DP} *1	±1	A
Source current (Body Diode)	Continuous	I_S	125	mA
	Pulsed	I_{SP} *1	1	A
Power dissipation		P_D *2	150	mW / TOTAL
			120	mW / ELEMENT
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%

*2 Each terminal mounted on a recommended land.

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	833	°C / W /TOTAL
		1042	°C / W /ELEMENT

* Each terminal mounted on a recommended land.

●**Electrical characteristics** (Ta = 25°C)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±10	μA	V_{GS}=±20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	-	-	V	I_D=1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	V_{DS}=60V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	1.0	-	2.3	V	V_{DS}=10V, I_D=1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	-	1.7	2.4	Ω	I_D=250mA, V_{GS}=10V
		-	2.1	3.0		I_D=250mA, V_{GS}=4.5V
		-	2.3	3.2		I_D=250mA, V_{GS}=4.0V
		-	3.0	12.0		I_D=10mA, V_{GS}=2.5V
Forward transfer admittance	$\lvert Y_{fs} \rvert$*	0.25	-	-	S	I_D=250mA, V_{DS}=10V
Input capacitance	C_{iss}	-	15	-	pF	V_{DS}=25V
Output capacitance	C_{oss}	-	4.5	-	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	-	2.0	-	pF	f=1MHz
Turn-on delay time	$t_{d(on)}$*	-	3.5	-	ns	I_D=100mA, V_{DD}≒ 30V
Rise time	t_r *	-	5	-	ns	V_{GS}=10V
Turn-off delay time	$t_{d(off)}$*	-	18	-	ns	R_L≒ 300Ω
Fall time	t_f *	-	28	-	ns	R_G=10Ω

*Pulsed

●**Body diode characteristics** (Source-Drain) (Ta = 25°C)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}*	-	-	1.2	V	I_s=250mA, V_{GS}=0V

*Pulsed

●Electrical characteristic curves

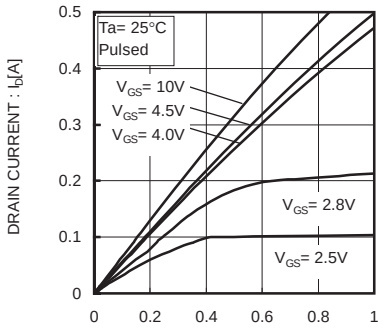


Fig.1 Typical Output Characteristics(Ⅰ)

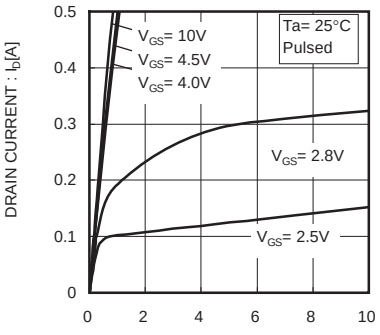


Fig.2 Typical Output Characteristics(Ⅱ)

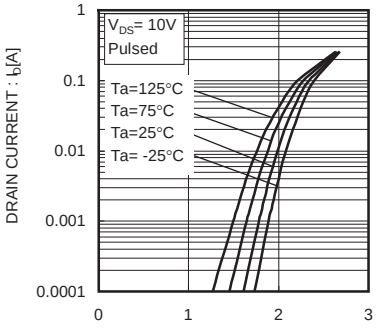


Fig.3 Typical Transfer Characteristics

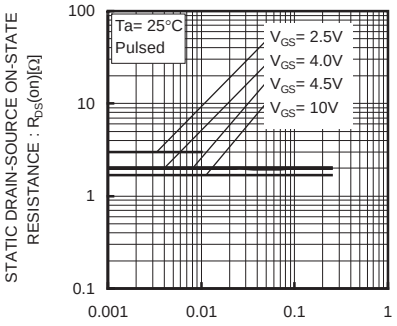


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(Ⅰ)

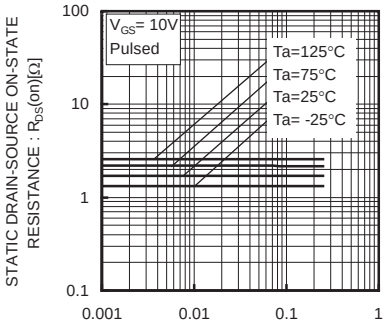


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(Ⅱ)

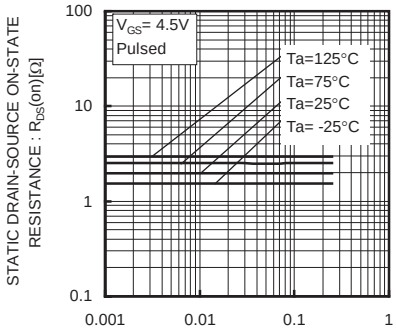


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)

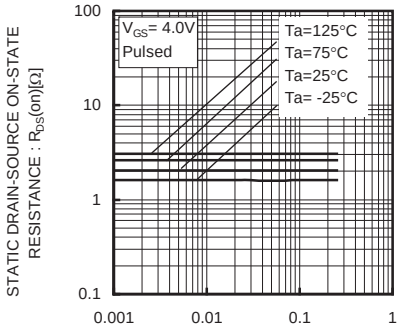


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(Ⅳ)

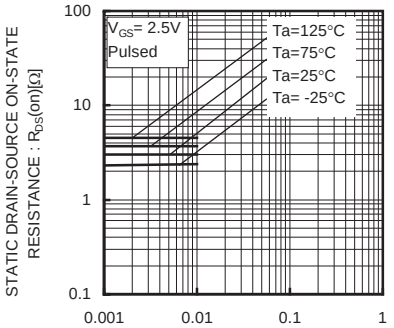


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(Ⅳ)

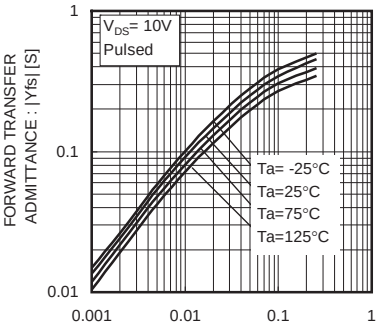


Fig.9 Forward Transfer Admittance vs. Drain Current

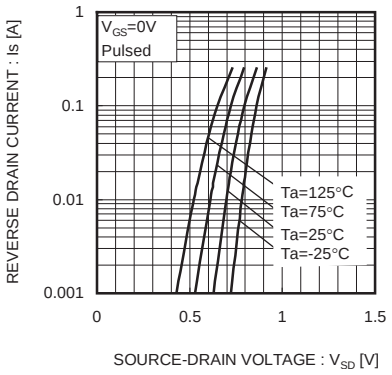


Fig.10 Reverse Drain Current vs. Sourse-Drain Voltage

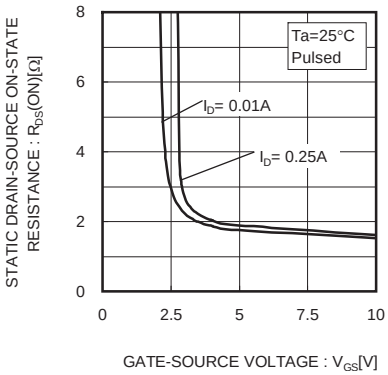


Fig.11 Static Drain-Source On-State Resistance vs. Gate Source Voltage

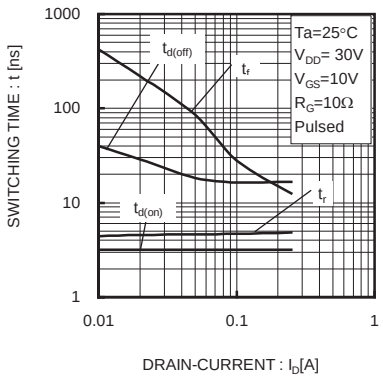


Fig.12 Switching Characteristics

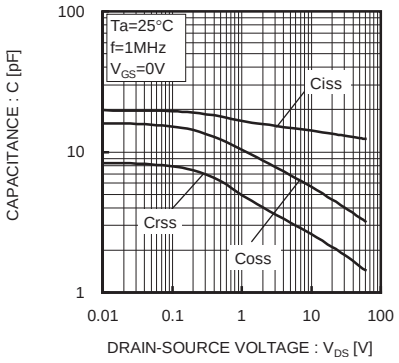


Fig.13 Typical Capacitance vs. Drain-Source Voltage

●Measurement circuits

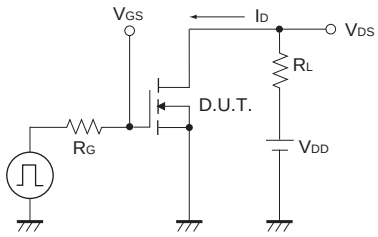


Fig.1-1 Switching time measurement circuit

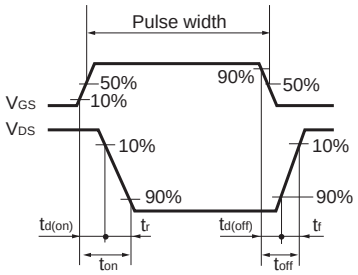


Fig.1-2 Switching waveforms

●Notice

This product might cause chip aging and breakdown under the large electrified environment.
Please consider to design ESD protection circuit.

Notes

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